TOSHIBA POWER MOS FET MODULE SILICON N CHANNEL MOS TYPE (L^2-π-MOSⅤ 4 IN 1)

MP4410

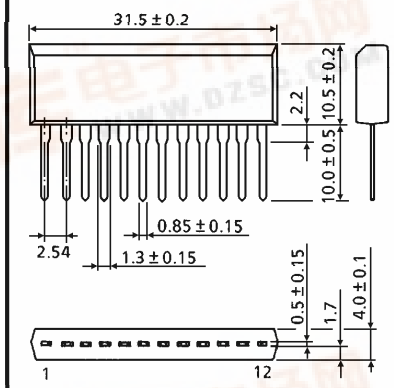
HIGH POWER, HIGH SPEED SWITCHING APPLICATIONS

HAMMER DRIVE, PULSE MOTOR DRIVE AND INDUCTIVE LOAD SWITCHING

INDUSTRIAL APPLICATIONS

- 4-Volt Gate Drive Available
- Small Package by Full Molding (SIP 12 Pin)
- High Drain Power Dissipation (4 Devices Operation)
  : P_T = 28W (Tc = 25°C)
- Low Drain-Source ON Resistance : $R_{DS\,(ON)}$ = 0.12Ω (Typ.)
- Low Leakage Current : I_{GSS} = ±10μA (Max.) (V_{GS} = ±16V)
  I_{DSS} = 100μA (Max.) (V_{DS} = 60V)
- Enhancement-Mode : V_{th} = 0.8~2.0V (I_D = 1mA)

Unit in mm



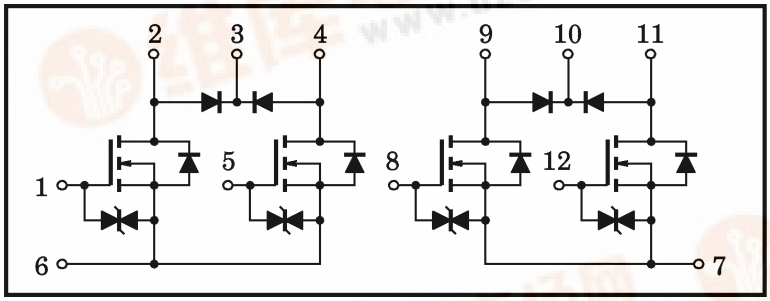
MOS FET		DIODE	
1, 5, 8, 12	GATE	2, 4, 9, 11	ANODE
2, 4, 9, 11	DRAIN	3, 10	CATHODE
6, 7	SOURCE		

JEDEC	—
EIAJ	—
TOSHIBA	2-32C1D

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Drain-Source Voltage		V_{DSS}	60	V
Gate-Source Voltage		V_{GSS}	±20	V
Drain Current		I_D	5	A
Peak Drain Current		I_{DP}	20	
Drain Power Dissipation (1 Device Operation)		P_D	2.2	W
Drain Power Dissipation (4 Devices Operation)	Ta = 25°C	P_T	4.4	W
	Tc = 25°C		28	
Channel Temperature		T_{ch}	150	°C
Storage Temperature Range		T_{stg}	−55~150	°C

ARRAY CONFIGURATION



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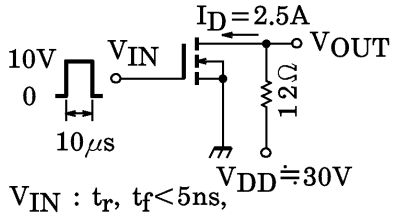
THERMAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	MAX.	UNIT
Thermal Resistance of Channel to Ambient (4 Devices Operation, Ta = 25°C)	$\Sigma R_{th\,(ch\text{-}a)}$	28.4	°C / W
Thermal Resistance of Channel to Case (4 Devices Operation, Tc = 25°C)	$\Sigma R_{th\,(ch\text{-}c)}$	4.46	°C / W
Maximum Lead Temperature for Soldering Purposes (3.2mm from Case for 10s)	T_L	260	°C

This Transistor is an Electrostatic Sensitive Device. Please Handle with Caution.

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current		I_{GSS}	$V_{GS} = \pm 16V$, $V_{DS} = 0$	—	—	±10	μA
Drain Cut-off Current		I_{DSS}	$V_{DS} = 60V$, $V_{GS} = 0$	—	—	100	μA
Drain-Source Breakdown Voltage		$V_{(BR)\,DSS}$	$I_D = 10mA$, $V_{GS} = 0$	60	—	—	V
Gate Threshold Voltage		V_{th}	$V_{DS} = 10V$, $I_D = 1mA$	0.8	—	2.0	V
Forward Transfer Admittance		$\|Y_{fs}\|$	$V_{DS} = 10V$, $I_D = 2.5A$	3.0	5.0	—	S
Drain-Source ON Resistance		$R_{DS\,(ON)}$	$I_D = 2.5A$, $V_{GS} = 4V$	—	0.21	0.31	Ω
			$I_D = 2.5A$, $V_{GS} = 10V$	—	0.12	0.16	
Input Capacitance		C_{iss}	$V_{DS} = 10V$, $V_{GS} = 0$, f = 1MHz	—	370	—	pF
Reverse Transfer Capacitance		C_{rss}		—	60	—	
Output Capacitance		C_{oss}		—	180	—	
Switching Time	Rise Time	t_r	 V_{IN} : t_r, $t_f < 5ns$, Duty Cycle ≦ 1%	—	18	—	ns
	Turn-on Time	t_{on}		—	25	—	
	Fall Time	t_f		—	15	—	
	Turn-off Time	t_{off}		—	170	—	
Total Gate Charge (Gate-Source Plus Gate-Drain)		Q_g	$I_D = 5A$, $V_{GS} = 10V$, $V_{DD} = 48V$	—	12	—	nC
Gate-Source Charge		Q_{gs}		—	8	—	
Gate-Drain ("Miller") Charge		Q_{gd}		—	4	—	

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Drain Reverse Current	I_{DR}	—	—	—	5	A
Peak Drain Reverse Current	I_{DRP}	—	—	—	20	A
Diode Forward Voltage	V_{DSF}	I_{DR} = 5A, V_{GS} = 0	—		−1.7	V

FLYBACK-DIODE RATINGS AND CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Maximum Forward Current	I_{FM}	—	—	—	5	A
Reverse Current	I_R	V_R = 120V	—	—	0.4	μA
Reverse Voltage	V_R	I_R = 100μA	120	—	—	V
Forward Voltage	V_F	I_F = 1A	—	—	1.8	V